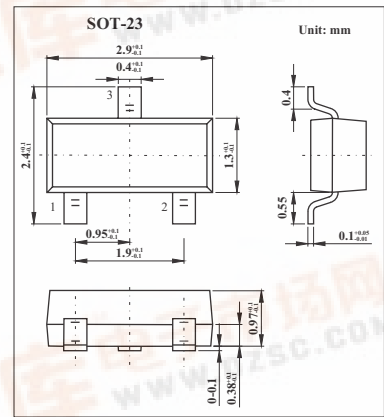


SMD Type Diodes

Schottky barrier (double) diodes  
BAS70 series

Features

- Low forward current
- High breakdown voltage
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	VR			70	V
Continuous forward current	IF			70	mA
Repetitive peak forward current	IFRM	tp ≤ 1 s; δ ≤ 0.5		70	mA
Non-repetitive peak forward current	IFSM	tp < 10 ms		100	mA
Storage temperature	Tstg		-65	+150	°C
Junction temperature	Tj			150	°C
Operating ambient temperature	Tamb		-65	+150	°C
thermal resistance from junction to ambient	Rthj-a			500	K/W

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Max	Unit
Forward voltage	VF	IF = 1 mA	410	mV
		IF = 10 mA	750	mV
		IF = 15 mA	1	V
Reverse voltage leakage current	IR	VR = 50 V; note 1	100	nA
		VR = 70 V; note 1	10	μA
Charge carrier life time (Krakauer method)	τ	IF = 5 mA	100	ps
Diode capacitance	Cd	f = 1 MHz; VR = 0;	2	pF

Note

1. Pulse test: tp = 300 μs; δ = 0.02

Marking

Type	BAS70	BAS70-04	BAS70-05	BAS70-06	BAS70-07
Marking	73*	74*	75*	76*	77p

